Amendments to the Specification:

Please replace the paragraph beginning at page 17, line 10, with the following amended paragraph:

Thereafter, the amorphous semiconductor film 105 is etched to be removed. This etching is performed by dry etching using NF_3 or CF_4, dry etching using ClF_3 without using plasma ~~generated from ClF_3~~, or wet etching using an alkali solution such as an aqueous solution containing hydrazine or tetraethylammonium hydroxide (chemical formula: $(CH_3)_4NOH$).

Please replace the paragraph beginning at page 26, line 13, with the following amended paragraph:

Thereafter, the amorphous ~~silicone~~ silicon film 505 is selectively etched to be removed. This etching is performed by dry etching using ClF_3 without the use of plasma ~~generated from ClF_3~~, or wet etching using an alkali solution such as an aqueous solution containing hydrazine or tetraethylammonium hydroxide (chemical formula: $(CH_3)_4NOH$). At this time, the barrier layer 504 functions as an etching stopper. Thereafter, the barrier layer 504 should be removed with hydrofluoric acid.

Please replace the paragraph beginning at page 28, line 11, with the following amended paragraph:

The following will describe, as the present embodiment, an embodiment wherein the surface of the crystalline silicon film is subjected to anisotropic etching in the process for producing the photoelectric conversion device described as the embodiment 1, 2 or 3, so as to make ~~one~~ I-layer in the photoelectric conversion device uneven. The

technique wherein the surface is made uneven to reduce the surface reflection of the photoelectric conversion device is called texture ~~technique~~ treatment.

Please replace the paragraph bridging pages 29 and 30 with the following amended paragraph:

The texture treatment is conducted by heating an aqueous solution having a sodium hydroxide concentration of 2% to 80°C. Under this condition, the etching rate of the crystalline silicon film 303 used in the present embodiment can be about 1 μm/minute. The etching is performed for 5 minutes. Thereafter, the workpiece is immersed into boiling water in order to stop the reaction instantaneously. Furthermore, the workpiece is sufficiently washed with flowing water. When the surface of the crystalline silicon film 303 after the texture treatment is observed with an electron microscope, irregularities, which are arranged at random and have a height of about [[1]] 0.1 to 5 μm, can be observed.

Please replace the paragraph beginning at page 36, line 12, with the following amended paragraph:

Thereafter, the amorphous semiconductor film 105 is etched to be removed. This etching is performed by dry etching using NF_3 or CF_4, dry etching using ClF_3 without the use of plasma ~~generated from ClF_3~~, or wet etching using an alkali solution such as an aqueous solution containing hydrazine or tetraethylammonium hydroxide (chemical formula: $(CH_3)_4(NOH)$).